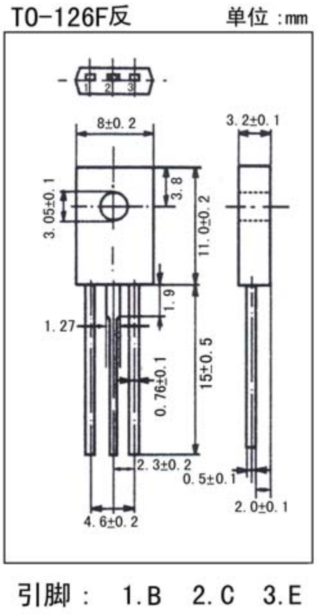
MJE13002F6(3DD13002F6) 硅NPN半导体三极管/SILICON NPN TRANSISTOR

用途:主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications，converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

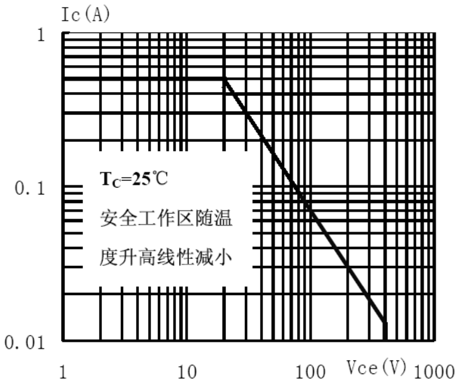
参数符号 Symbol	数值 Rating	单位 Unit
V_{CBO}	600	V
V_{CEO}	400	V
V_{EBO}	9.0	V
I_C	0.5	A
P_C(Ta=25℃)	1.25	W
P_C(T_C=25℃)	20	W
T_j	150	℃
T_{stg}	-55～150	℃



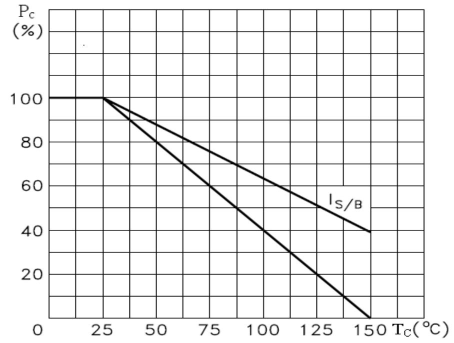
电性能参数/Electrical characteristics(Ta=25℃)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V_{CBO}	I_C=1mA I_E=0	600			V
V_{CEO}	I_C=10mA I_B=0	400			V
V_{EBO}	I_E=1mA I_C=0	9.0			V
I_{CBO}	V_{CB}=600V I_E=0			0.1	mA
I_{CEO}	V_{CE}=400V I_B=0			0.1	mA
I_{EBO}	V_{EB}=9.0V I_C=0			0.1	mA
h_{FE}	V_{CE}=5.0V I_C=200mA	10		40	
$V_{CE(sat)}$	I_C=200mA I_B=40mA			0.5	V
$V_{BE(sat)}$	I_C=200mA I_B=40mA			1.2	V
f_T	V_{CE}=10V I_C=50mA f=1.0MHz	5.0			MHz
t_f	V_{CE}=5V I_C=100mA (UI9600)			0.6	μs
t_S				4.0	μs

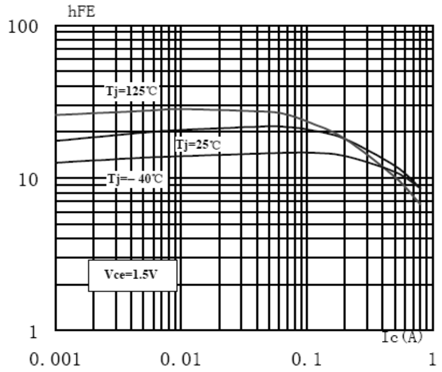
SOA(DC)



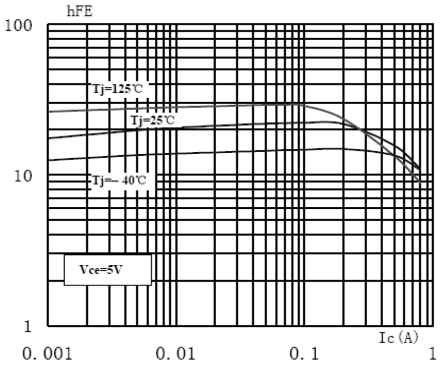
P_C-T_C



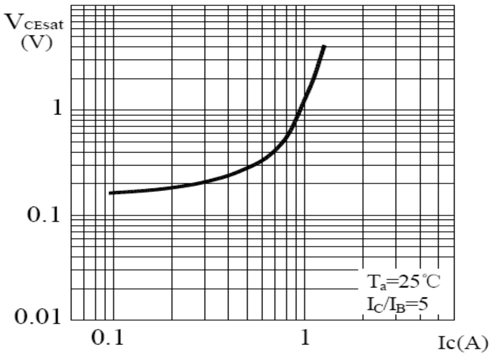
h_{FE}-Ic



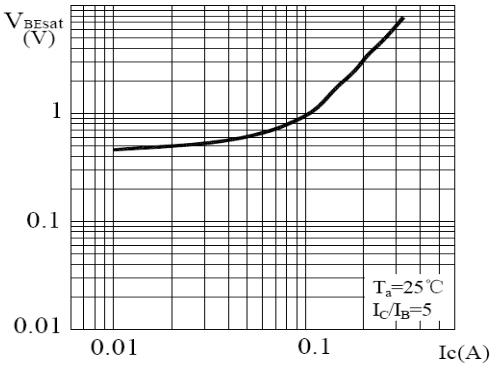
h_{FE}-Ic



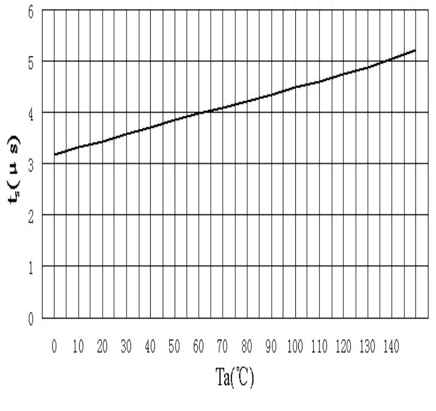
Vces-I_C



Vbes-I_C



t_S-Ta



h_{FE}-Ta